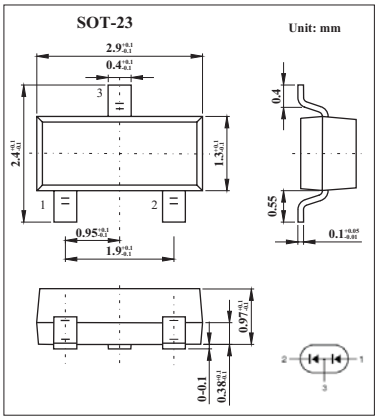
High-Speed Double Diode

KAV99(BAV99)



■ Features

- Small plastic SMD package.
- High switching sped: max.4 ns.
- Repetitive peak forward current: max.450 mA.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}	85	V
Continuous reverse voltage	V_R	75	V
Continuous forward current(single diode loaded *) (double diode loaded *)	I_F	215 125	mA
Repetitive peak forward current	I_{FRM}	450	mA
Non-repetitive peak forward current Tj=25 ℃ t=1 μ s	I_{FSM}	4	A
t=1ms		1	
t=1s		0.5	
power dissipation *	P_D	250	mW
Thermal resistance from junction to tie-point	$R_{th\ j\text{-}tp}$	360	K/W
Thermal resistance from junction to ambient *	$R_{th\ j\text{-}a}$	500	K/W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-65 to +150	℃

* Device mounted on an FR4 printed-circuit board.

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Max	Unit
Forward voltage	V_F	I_F =1 mA	715	mV
		I_F =10 mA	855	mV
		I_F =50 mA	1	V
		I_F =150 mA	1.25	V
Reverse current	I_R	V_R =25 V	30	nA
		V_R =75 V	1	μ A
		V_R =25 V; Tj= 150 ℃	30	μ A
		V_R =75 V; Tj= 150 ℃	50	μ A
Diode capacitance	C_d	V_R =0 V, f= 1 MHz	1.5	pF
Reverse recovery time	t_{rr}	when switched from I_F= 10 mA to I_R=10mA;R_L=100 Ω ; measured at I_R= 1mA	4	nS
Forward recovery voltage	V_{fr}	I_F = 10 mA, tr= 20 ns	1.75	V

■ Marking

Marking	A7

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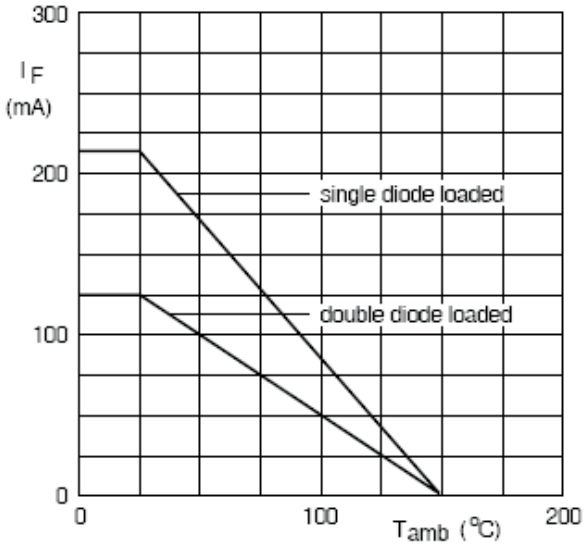
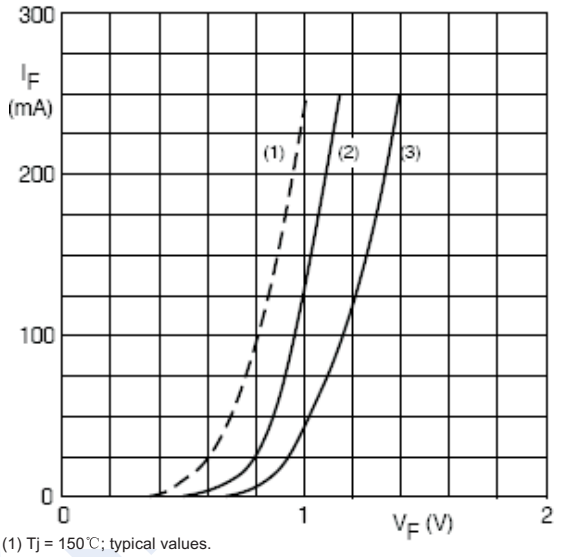
■ Typical Characteristics



Device mounted on an FR4 printed-circuit board.

Fig.1Maximum permissible continuous forward current as a function of ambient temperature.

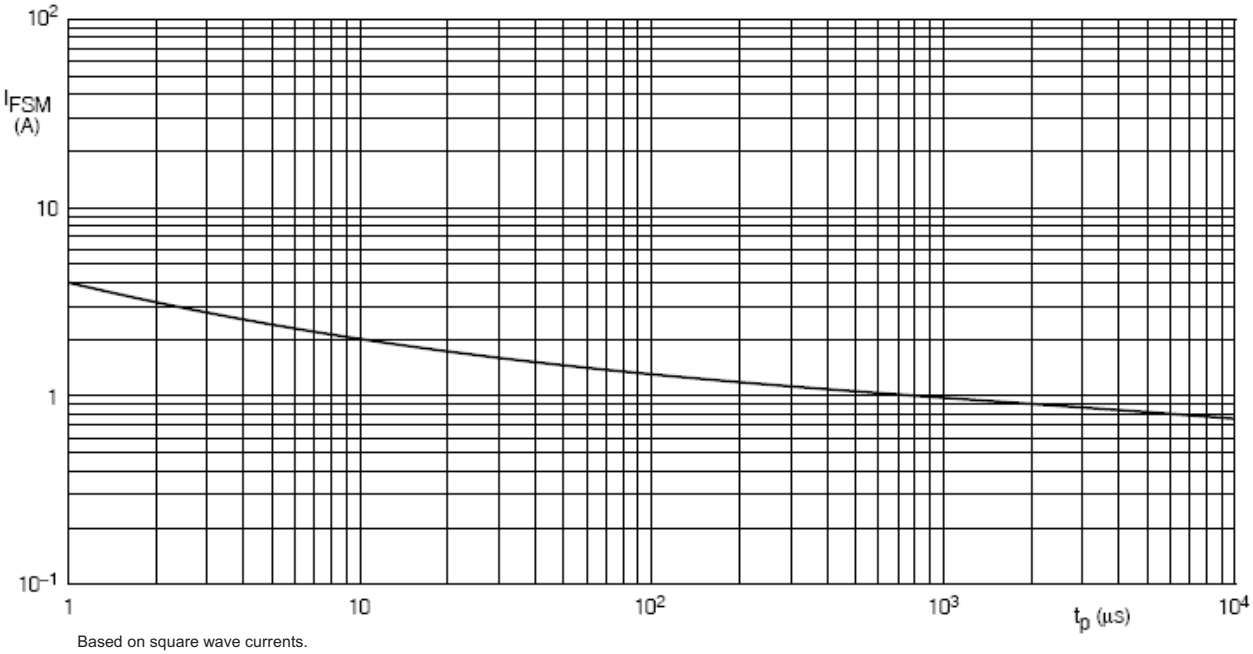


(1) Tj = 150℃; typical values.

(2) Tj = 25℃; typical values.

(3) Tj = 25℃; maximum values.

Fig.2 Forward current as a function of forward voltage.



Based on square wave currents.

Tj = 25℃ prior to surge.

Fig.3 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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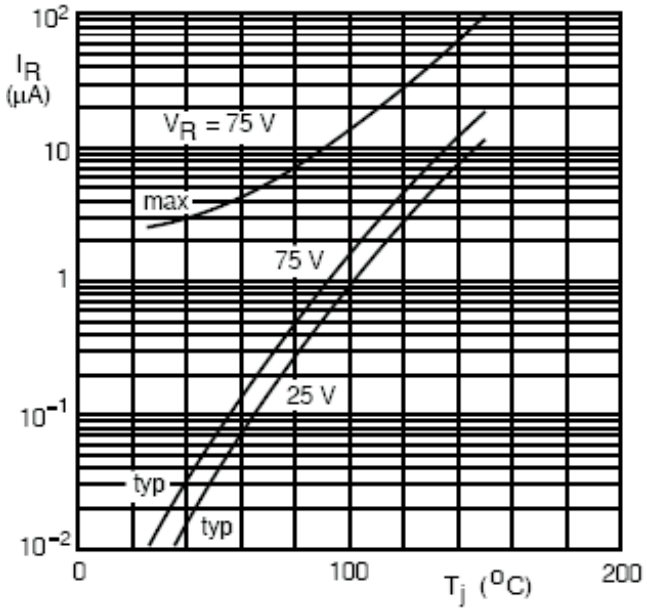
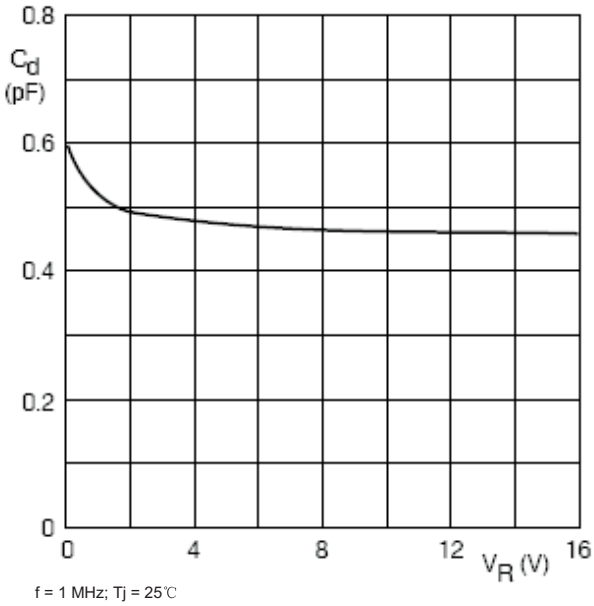


Fig.4 Reverse current as a function of junction temperature.



f = 1 MHz; Tj = 25℃

Fig.5 Diode capacitance as a function of reverse voltage; typical values.